# NTLUD3A50PZ

# MOSFET – Power, Dual, P-Channel, μCool, UDFN, 2.0x2.0x0.55 mm
## -20 V, -5.6 A

**ON Semiconductor®**

**http://onsemi.com**

### Features

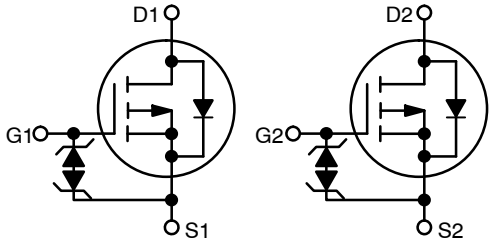
- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low $R_{DS(on)}$
- Low Profile UDFN 2.0x2.0x0.55 mm for Board Space Saving
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- High Side Load Switch
- Reverse Current Protection
- Battery Switch
- Optimized for Power Management Applications for Portable Products, such as Cell Phones, PMP, DSC, GPS, and others

**MOSFET**

| $V_{(BR)DSS}$ | $R_{DS(on)}$ MAX | $I_D$ MAX |
|---|---|---|
| −20 V | 50 mΩ @ −4.5 V | −5.6 A |
| | 70 mΩ @ −2.5 V | |
| | 115 mΩ @ −1.8 V | |
| | 175 mΩ @ −1.5 V | |




P−Channel MOSFET

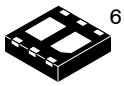
**MAXIMUM RATINGS** ($T_J$ = 25°C unless otherwise stated)

| Parameter | | | Symbol | Value | Units |
|---|---|---|---|---|---|
| Drain-to-Source Voltage | | | $V_{DSS}$ | −20 | V |
| Gate-to-Source Voltage | | | $V_{GS}$ | ±8.0 | V |
| Continuous Drain Current (Note 1) | Steady State | $T_A$ = 25°C | $I_D$ | −4.4 | A |
| | | $T_A$ = 85°C | | −3.2 | |
| | t ≤ 5 s | $T_A$ = 25°C | | −5.6 | |
| Power Dissipation (Note 1) | Steady State | $T_A$ = 25°C | $P_D$ | 1.4 | W |
| | t ≤ 5 s | $T_A$ = 25°C | | 2.2 | |
| Continuous Drain Current (Note 2) | Steady State | $T_A$ = 25°C | $I_D$ | −2.8 | A |
| | | $T_A$ = 85°C | | −2.0 | |
| Power Dissipation (Note 2) | | $T_A$ = 25°C | $P_D$ | 0.5 | W |
| Pulsed Drain Current | | tp = 10 μs | $I_{DM}$ | −13 | A |
| Operating Junction and Storage Temperature | | | $T_J$, $T_{STG}$ | -55 to 150 | °C |
| ESD (HBM, JESD22−A114)<br>(MM, JESD22−A114) | | | $V_{ESD}$ | 1400<br>200 | V |
| Source Current (Body Diode) (Note 2) | | | $I_S$ | −1.0 | A |
| Lead Temperature for Soldering Purposes (1/8″ from case for 10 s) | | | $T_L$ | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces) based on both FETs on.

**MARKING DIAGRAM**

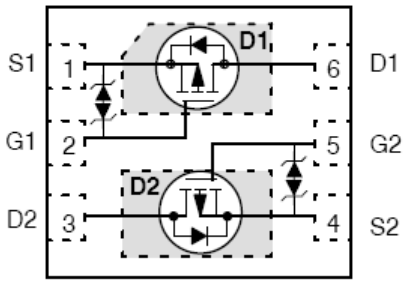



**UDFN6**
**CASE 517BF**
**μCOOL™**


AA = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

**PIN CONNECTIONS**




(Top View)

**ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

2. Surface-mounted on FR4 board using the minimum recommended pad size of 30 $mm^2$, 1 oz. Cu based on both FETs on.

**THERMAL RESISTANCE RATINGS**

| Parameter | Symbol | Max | Units |
|---|---|---|---|
| Junction-to-Ambient – Steady State (Note 3) | $R_{\theta JA}$ | 91 | °C/W |
| Junction-to-Ambient – t ≤ 5 s (Note 3) | $R_{\theta JA}$ | 57 | |
| Junction-to-Ambient – Steady State min Pad (Note 4) | $R_{\theta JA}$ | 228 | |

**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0 V, $I_D$ = −250 μA | | −20 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | $I_D$ = −250 μA, ref to 25°C | | | −13 | | mV/°C |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{GS}$ = 0 V, $V_{DS}$ = −20 V | $T_J$ = 25°C | | | −1.0 | μA |
| Gate-to-Source Leakage Current | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ±5.0 V | | | | ±5.0 | μA |
| **ON CHARACTERISTICS** (Note 5) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS}$ = $V_{DS}$, $I_D$ = −250 μA | | −0.4 | | −1.0 | V |
| Negative Threshold Temp. Coefficient | $V_{GS(TH)}/T_J$ | | | | 3.0 | | mV/°C |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS}$ = −4.5 V, $I_D$ = −4.0 A | | | 37 | 50 | mΩ |
| | | $V_{GS}$ = −2.5 V, $I_D$ = −3.0 A | | | 46 | 70 | |
| | | $V_{GS}$ = −1.8 V, $I_D$ = −2.0 A | | | 63 | 115 | |
| | | $V_{GS}$ = −1.5 V, $I_D$ = −1.0 A | | | 86 | 175 | |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ = −5.0 V, $I_D$ = −3.0 A | | | 16 | | S |
| **CHARGES AND CAPACITANCES** | | | | | | | |
| Input Capacitance | $C_{ISS}$ | $V_{GS}$ = 0 V, f = 1 MHz, $V_{DS}$ = −15 V | | | 920 | | pF |
| Output Capacitance | $C_{OSS}$ | | | | 85 | | |
| Reverse Transfer Capacitance | $C_{RSS}$ | | | | 80 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = −4.5 V, $V_{DS}$ = −15 V; $I_D$ = −3.0 A | | | 10.4 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | | 0.5 | | |
| Gate-to-Source Charge | $Q_{GS}$ | | | | 1.2 | | |
| Gate-to-Drain Charge | $Q_{GD}$ | | | | 3.0 | | |
| **SWITCHING CHARACTERISTICS, VGS = 4.5 V** (Note 6) | | | | | | | |
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS}$ = −4.5 V, $V_{DD}$ = −15 V, $I_D$ = −3.0 A, $R_G$ = 1 Ω | | | 7.0 | | ns |
| Rise Time | $t_r$ | | | | 12 | | |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | | | 39 | | |
| Fall Time | $t_f$ | | | | 30 | | |
| **DRAIN-SOURCE DIODE CHARACTERISTICS** | | | | | | | |
| Forward Diode Voltage | VSD | $V_{GS}$ = 0 V, $I_S$ = −1.0 A | $T_J$ = 25°C | | −0.67 | −1.0 | V |
| | | | $T_J$ = 125°C | | −0.56 | | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces) based on both FETs on.
4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 $mm^2$, 1 oz. Cu based on both FETs on.
5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **DRAIN-SOURCE DIODE CHARACTERISTICS** | | | | | | |
| Reverse Recovery Time | $t_{RR}$ | $V_{GS}$ = 0 V, dis/dt = 100 A/μs, $I_S$ = −1.0 A | | 12.1 | | ns |
| Charge Time | $t_a$ | | | 6.4 | | |
| Discharge Time | $t_b$ | | | 5.7 | | |
| Reverse Recovery Charge | $Q_{RR}$ | | | 4.0 | | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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## TYPICAL CHARACTERISTICS

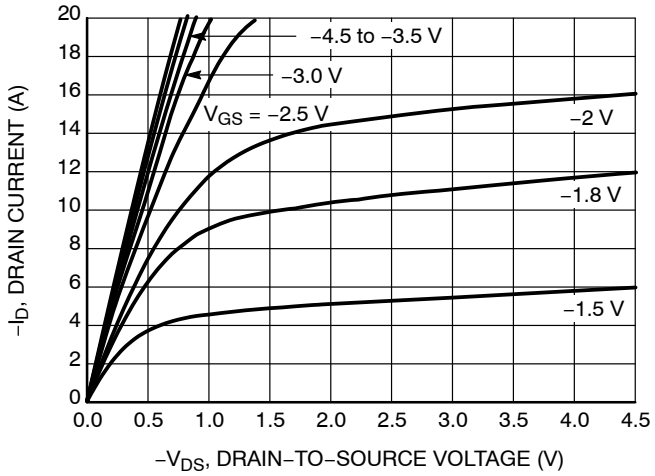



**Figure 1. On−Region Characteristics**

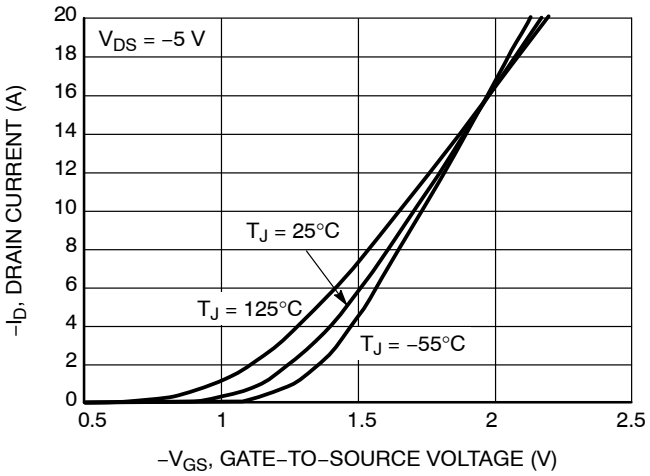



**Figure 2. Transfer Characteristics**

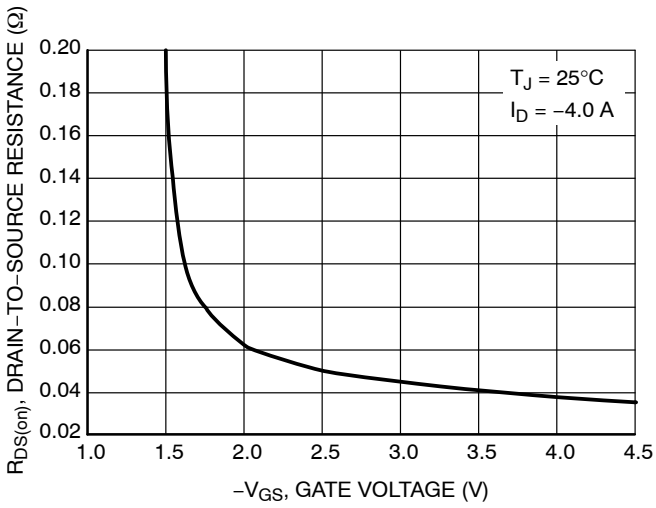



**Figure 3. On−Resistance vs. Gate−to−Source Voltage**

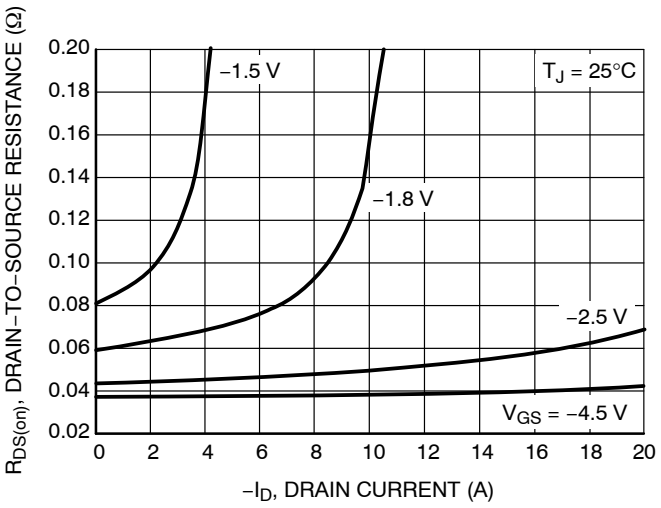



**Figure 4. On−Resistance vs. Drain Current and Gate Voltage**

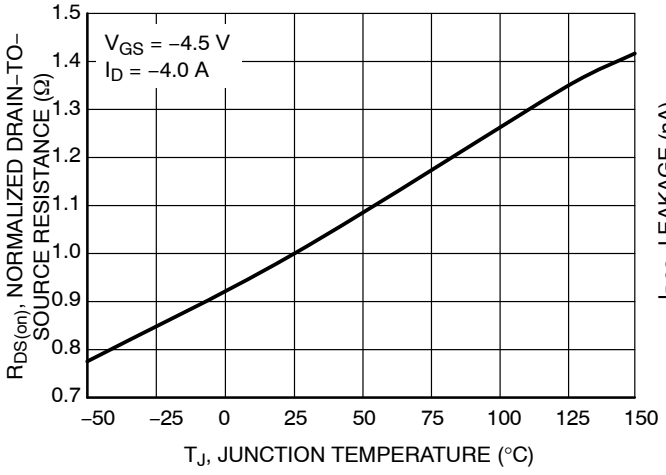



**Figure 5. On−Resistance Variation with Temperature**

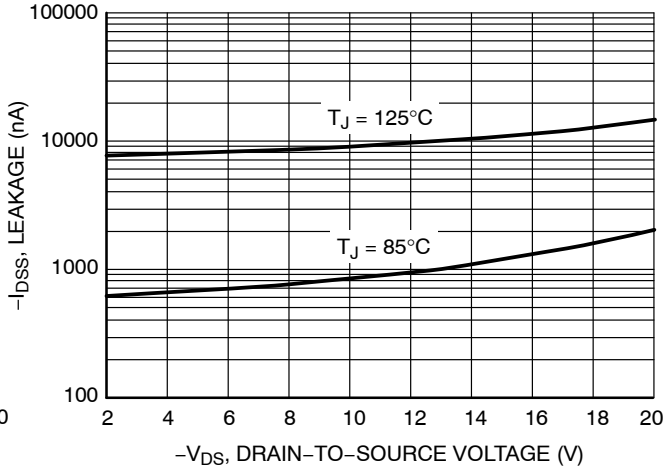



**Figure 6. Drain−to−Source Leakage Current vs. Voltage**

## TYPICAL CHARACTERISTICS

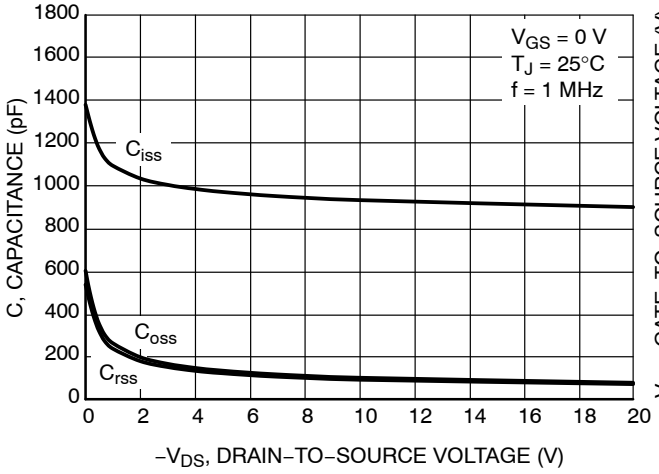



**Figure 7. Capacitance Variation**

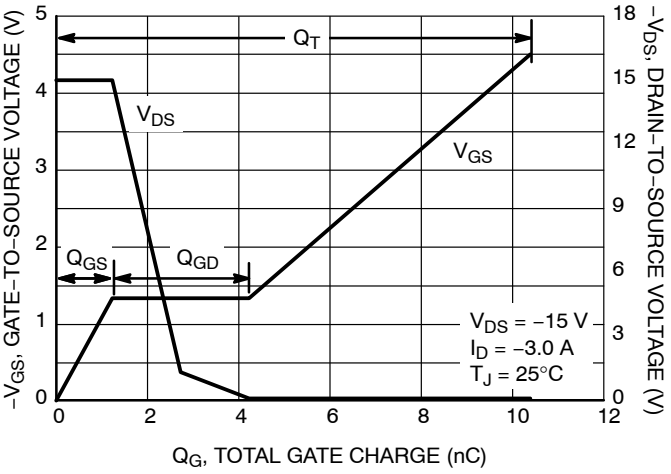



**Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge**

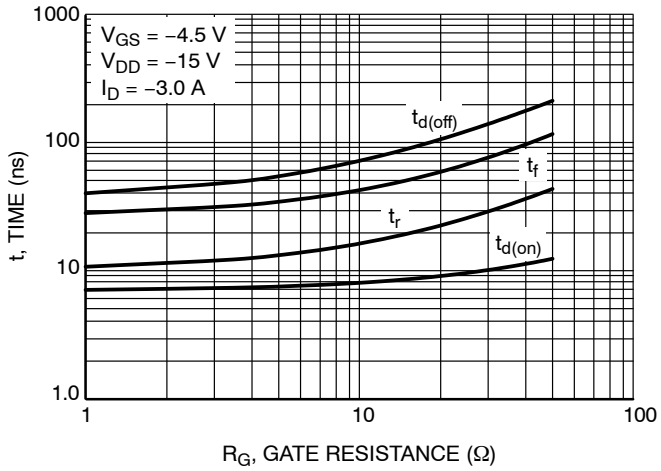



**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**

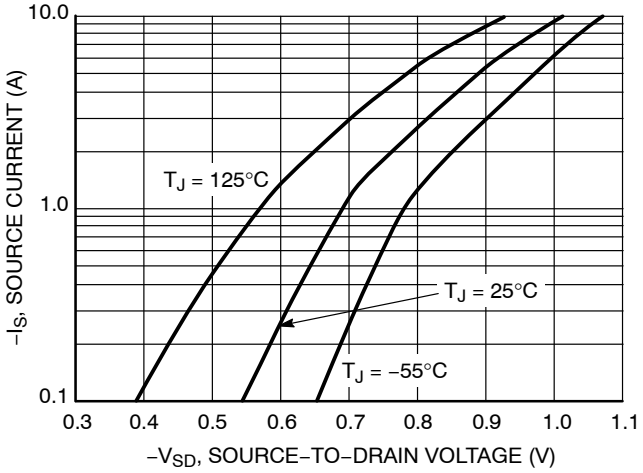



**Figure 10. Diode Forward Voltage vs. Current**

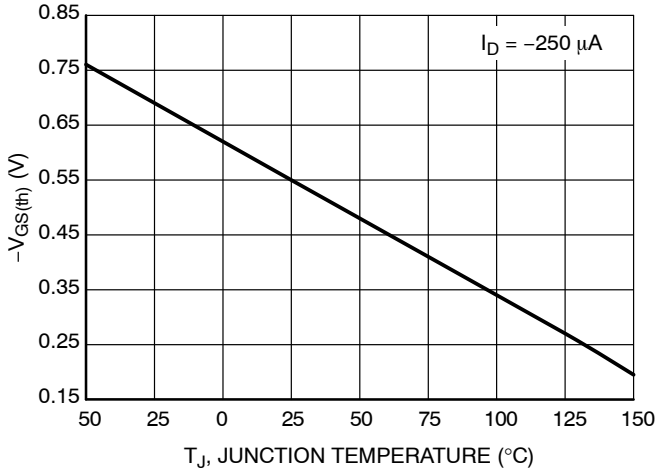



**Figure 11. Threshold Voltage**

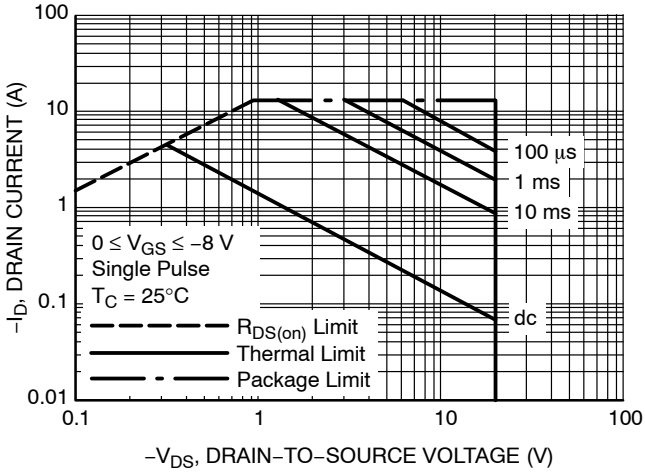



**Figure 12. Maximum Rated Forward Biased Safe Operating Area**

## TYPICAL CHARACTERISTICS

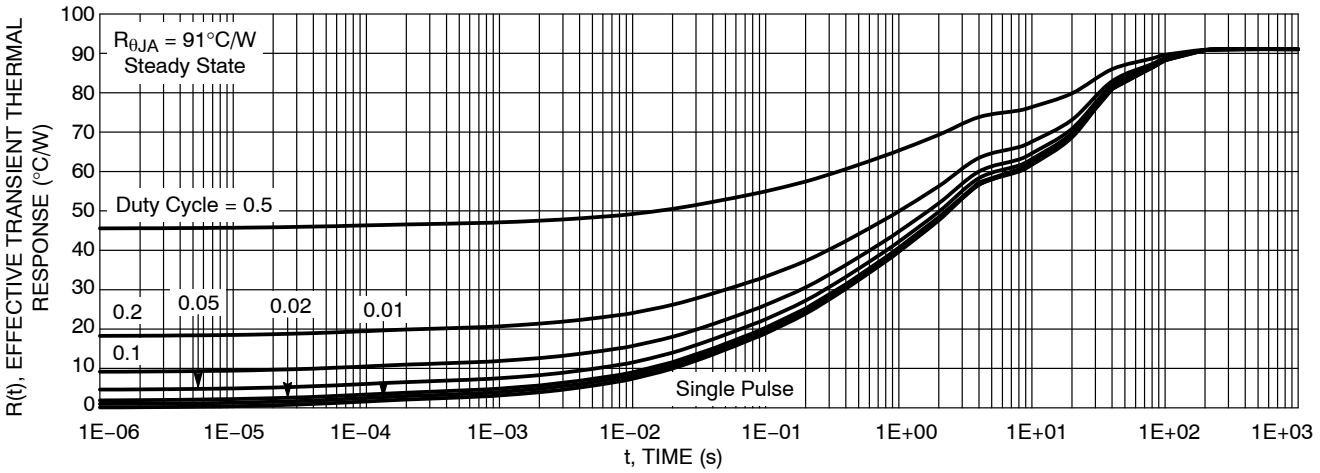



**Figure 13. FET Thermal Response**

### DEVICE ORDERING INFORMATION

| Device | Package | Shipping† |
|---|---|---|
| NTLUD3A50PZTAG | UDFN6<br>(Pb−Free) | 3000 / Tape & Reel |
| NTLUD3A50PZTBG | UDFN6<br>(Pb−Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

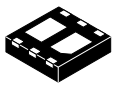
μCool is a trademark of Semiconductor Components Industries, LLC (SCILLC).

# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

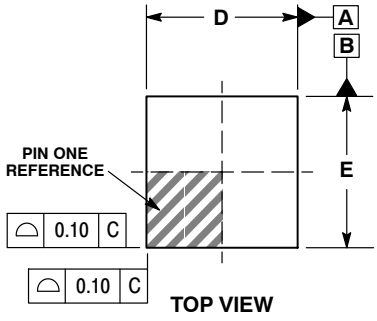
ON Semiconductor®

**UDFN6 2x2, 0.65P**
CASE 517BF
ISSUE B

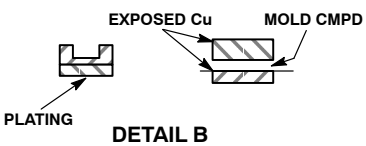
DATE 20 AUG 2012



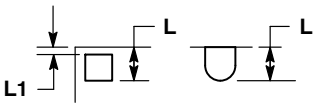
**SCALE 4:1**



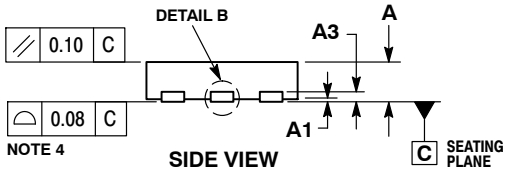

**TOP VIEW**



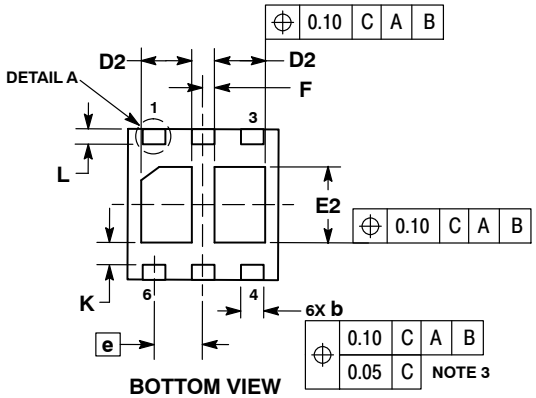

**DETAIL B**
**OPTIONAL CONSTRUCTIONS**




**DETAIL A**
**OPTIONAL CONSTRUCTIONS**




**SIDE VIEW**

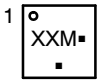



**BOTTOM VIEW**

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

| | MILLIMETERS | |
|---|---|---|
| DIM | MIN | MAX |
| A | 0.45 | 0.55 |
| A1 | 0.00 | 0.05 |
| A3 | 0.13 REF | |
| b | 0.25 | 0.35 |
| D | 2.00 BSC | |
| D2 | 0.57 | 0.77 |
| E | 2.00 BSC | |
| E2 | 0.90 | 1.10 |
| e | 0.65 BSC | |
| F | 0.15 BSC | |
| K | 0.25 REF | |
| L | 0.20 | 0.30 |
| L1 | --- | 0.10 |

### GENERIC MARKING DIAGRAM*

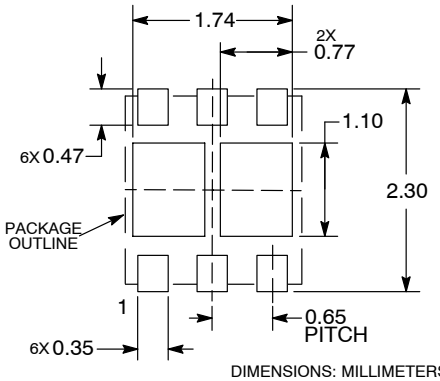



XX = Specific Device Code
M = Date Code

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present.

### RECOMMENDED MOUNTING FOOTPRINT




DIMENSIONS: MILLIMETERS

| | | | |
|---|---|---|---|
| **DOCUMENT NUMBER:** | **98AON48159E** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. | |
| **DESCRIPTION:** | **UDFN6 2X2, 0.65P** | | **PAGE 1 OF 1** |

## ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS**:
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**onsemi Website:** www.onsemi.com

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**For additional information, please contact your local Sales Representative at** www.onsemi.com/support/sales